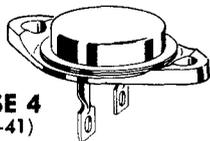


**2N1120 (GERMANIUM)**  
**2N1120 JAN AVAILABLE**

**$V_{CB} = 80\text{ V}$**   
 **$I_E = 15\text{ A}$**   
 **$P_D = 90\text{ W}$**



**CASE 4**  
(TO-41)

PNP germanium power transistors for military and industrial power applications.

**MAXIMUM RATINGS**

Rating	Symbol	2N1120	Unit
Collector-Emitter Voltage	$V_{CEO}$	40	Vdc
Collector-Emitter Voltage	$V_{CES}$	70	Vdc
Collector-Base Voltage	$V_{CB}$	80	Vdc
Emitter-Base Voltage	$V_{EB}$	40	Vdc
Emitter Current	$I_E$	15	Adc
Total Device Dissipation @ $T_C = 25^\circ\text{C}$ Derate above $25^\circ\text{C}$	$P_D$	90 1.2	Watts $\text{W}/^\circ\text{C}$
Operating Junction Temperature Range	$T_J$	-65 to +100	$^\circ\text{C}$

**THERMAL CHARACTERISTICS**

Characteristic	Symbol	Max	Unit
Thermal Resistance, Junction to Case	$\theta_{JC}$	0.8	$^\circ\text{C}/\text{W}$

**POWER-TEMPERATURE  
 DERATING CURVE**

